

PCT

WORLD INTELLECTUAL PROPERTY ORGANIZATION
International Bureau



9802846-7

1P015

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶: C08G 8/00, G03F 7/032	A1	(11) International Publication Number: WO 97/19969 (43) International Publication Date: 5 June 1997 (05.06.97)
(21) International Application Number: PCT/US96/18784 (22) International Filing Date: 21 November 1996 (21.11.96) (30) Priority Data: 08/562,867 27 November 1995 (27.11.95) US (71) Applicant: HOECHST CELANESE CORPORATION [US/US]; Route 202-206 North, Somerville, NJ 08876 (US). (72) Inventors: RAHMAN, M., Dalij; 62 Concord Ridge Road, Flemington, NJ 08822 (US). AUBIN, Daniel, P.; 202 Congdon Road, Voluntown, CT 06384 (US). (74) Agents: SAYKO, Andrew, F., Jr. et al.; Hoechst Celanese Corporation, 70 Meister Avenue, Sommerville, NJ 08876 (US).		(81) Designated States: CN, JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>
(54) Title: METAL ION REDUCTION IN PHOTORESIST COMPOSITIONS BY CHELATING ION EXCHANGE RESIN (57) Abstract The present invention provides methods for producing a photoresist having a very low level of metal ions, utilizing a treated chelating ion exchange resin to make the neutral ammonium salt or acid form. A method is also provided for producing semiconductor devices using such photoresist compositions.		